

Application Specific Discretes A.S.D.™

FEATURES

- UNIDIRECTIONAL FUNCTION
- PROGRAMMABLE BREAKDOWN VOLTAGE UP TO 250 V
- PROGRAMMABLE CURRENT LIMITATION FROM 40 mA TO 500 mA
- SURGE CURRENT CAPABILITY IPP = 30A 10/1000 μs

DESCRIPTION

Dedicated to sensitive telecom equipment protection, this device can provide both voltage and current triggered protection with a very tight tolerance. The breakdown voltage can be easily programmed by using an external zener diode.

A multiple protection mode can be also performed when using several zener diodes, providing to each line interface an optimized protection level. The current limiting function is achieved with the

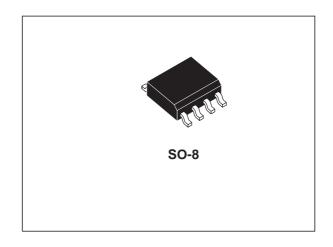
use of a resistor between the gate and the cathode. The value of the resistor will determine the level of the desired current.

COMPLIES WITH THE FOLLOWING STANDARDS :

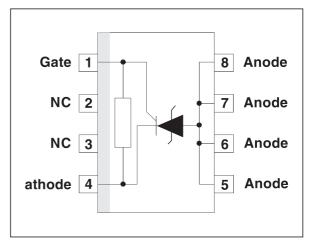
CCITT K17 :	10/700	μs	1.5 kV
	5/310	μs	38 A
VDE 0433 :	10/700	μs	2k V
	5/310	μs	40 A(*)
CNET :	0.5/700	μs	1.5 kV
	0.2/310	μs	38 A
FCC part 68 :	2/10	μs	2.5 kV
	2/10	μs	75 A(*)
BELLCORE	10/1000	μs	1 kV
TR-NWT-000974 :	10/1000	μs	30 A (*)

(*) with series resistors or PTC.





SCHEMATIC DIAGRAM



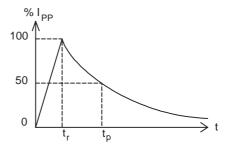
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ABSOLUTE MAXIMUM RATINGS (T_{amb} = 25 °C)

Symbol	Parameter	Value	Unit	
I _{PP}	Peak pulse current (see note 1)	10/1000μs 5/310μs 2/10μs	30 40 75	A
I _{TSM}	Non repetitive surge peak on-state current $(F = 50Hz)$	t _p = 10ms t = 1s	5 3.5	A
T _{stg} Tj	Storage temperature range Maximum junction temperature		- 55 to + 150 150	°C

Note 1 : Pulse waveform :

t _r =10μs	t _p =1000μs
t _r =5μs	t _p =310μs
t _r =2μs	t _p =10μs
	t _r =10μs t _r =5μs

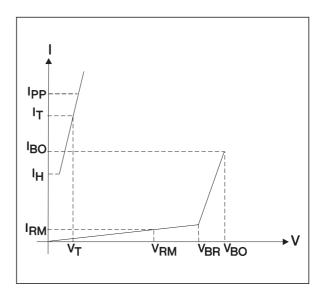


THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R _{th (j-a)}	Junction to ambient	170	°C/W

ELECTRICAL CHARACTERISTICS (T_{amb} = 25°C)

Symbol	Parameter
V _{RM}	Stand-off voltage
I _{RM}	Leakage current at stand-off voltage
V _{BR}	Breakdown voltage
V _{BO}	Breakover voltage
Iн	Holding current
I _{BO}	Breakover current
I _{PP}	Peak pulse current
V _{GN}	Gate voltage
IG	Gate triggering current
С	Capacitance



1 - OPERATION WITHOUT GATE

Туре	I _{RM} @	V _{RM}	V _{BR}	@ I _R	V _{во} @ І _{во}		I _H	С	
	max.		min.		max.	min. note1	max.	min. note 2	max. note 3
	μΑ	v	v	mA	v	mA	mA	mA	pF
TPP25011	6	60	250	1	340	15	200	180	100

2 - OPERATION WITH GATE

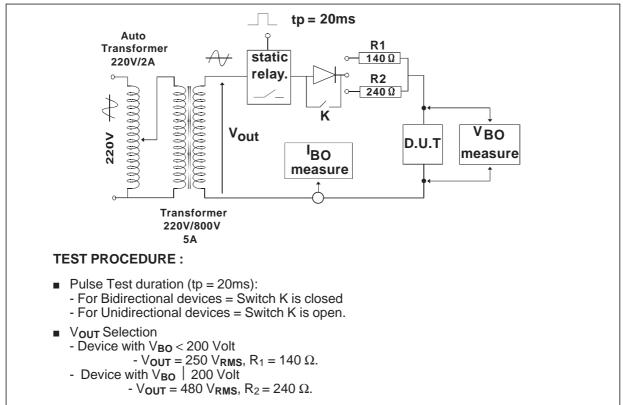
Туре	V _{GN} @ I _{GN} = 30 mA		l _G			
	min.	max.	min.	max.		
	not	e 4	$V_{A-C} = 100 V$			
	V V		mA	mA		
TPP25011	1.05	1.35	5	40		

Note 1: See the reference test circuit 1.

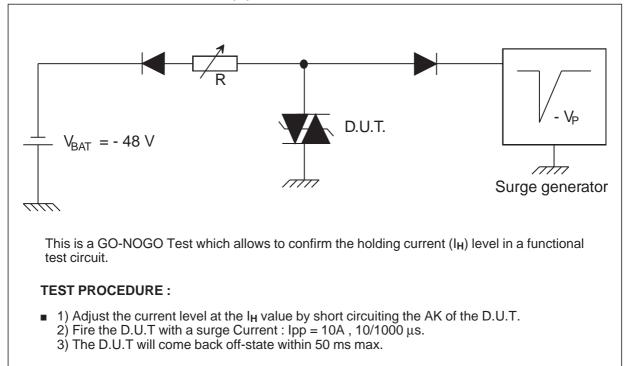
Note 2: See test circuit 2.

Note 3: $V_R = 5V, F = 1MHz$

REFERENCE TEST CIRCUIT 1 :



FUNCTIONAL HOLDING CURRENT (IH) TEST CIRCUIT 2 = GO - NOGO TEST



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APPLICATION CIRCUIT Overvoltage protection and current limitation

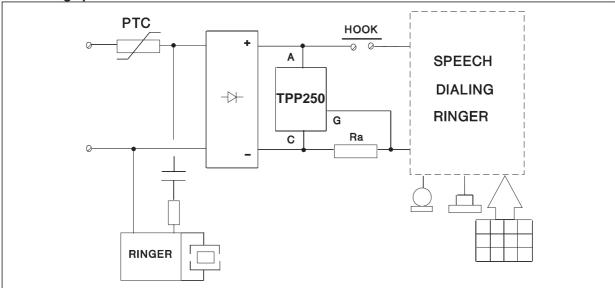
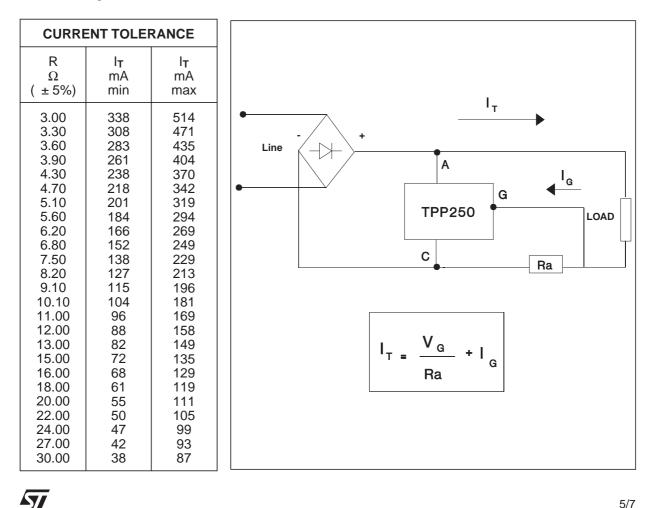
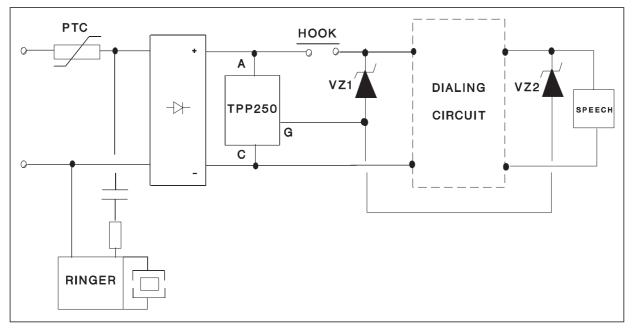


Table below gives the tolerance of the limited current IT for each standardized resistor value.



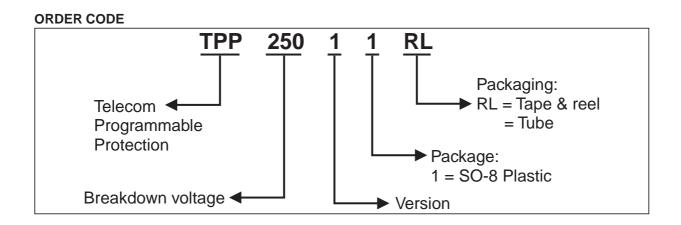
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Telephone set protection



PROTECTION MODES :

OFF HOOK = Ringer circuit protection is insured with intrinsic breakdown voltage at 250 V **ON HOOK** = In dialing mode and in conversation mode, the breakdown voltage of TPP250 can be adapted at different levels with zener diodes.

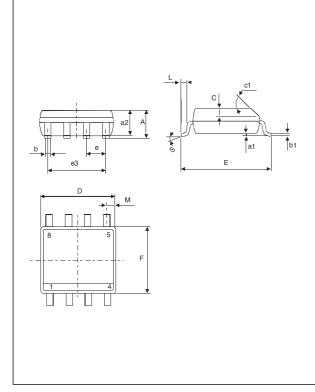


MARKING

Package	Туре	Marking	
SO-8	TPP25011	TPP250	

PACKAGE MECHANICAL DATA

SO-8 Plastic



	DIMENSIONS					
REF.	F. Millim		es	Inches		
	Min.	Тур.	Max.	Min.	Тур.	Max.
А			1.75			0.069
a1	0.1		0.25	0.004		0.010
a2			1.65			0.065
b	0.35		0.48	0.014		0.019
b1	0.19		0.25	0.007		0.010
С		0.50			0.020	
c1			45°	(typ)		
D	4.8		5.0	0.189		0.197
Е	5.8		6.2	0.228		0.244
е		1.27			0.050	
e3		3.81			0.150	
F	3.8		4.0	0.15		0.157
L	0.4		1.27	0.016		0.050
М			0.6			0.024
S	8° (max)					

Packaging : Products supplied antistatic tubes or tape and reel.

Weight :0.08g

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